

MA2Z331

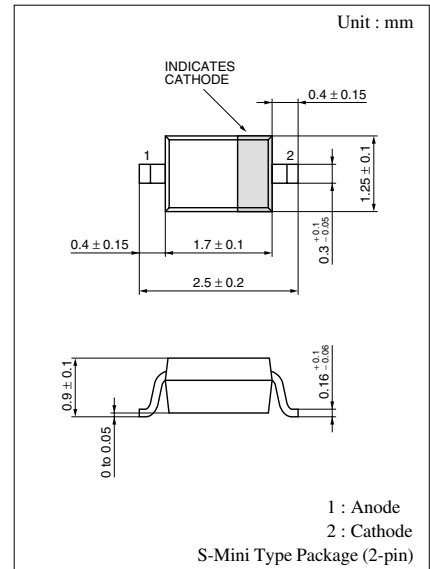
Silicon epitaxial planar type

■ Features

- Small series resistance r_D , $r_D = 0.18 \Omega$ (typ.)
- Good linearity of C – V curve
- Small type package, optimum for down-sizing of equipment

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	12	V
Forward current (DC)	I_F	20	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: 6T

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 12 \text{ V}$			10	nA
Diode capacitance	$C_{D(1V)}$	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$	17.0		20.0	pF
	$C_{D(2V)}$	$V_R = 2 \text{ V}, f = 1 \text{ MHz}$	14.0	15.0	16.0	pF
	$C_{D(4V)}$	$V_R = 4 \text{ V}, f = 1 \text{ MHz}$	10.0		12.4	pF
	$C_{D(10V)}$	$V_R = 10 \text{ V}, f = 1 \text{ MHz}$	5.5	6.0	6.5	pF
Capacitance ratio	$C_{D(1V)}/C_{D(4V)}$		1.53	1.6	1.83	—
	$C_{D(2V)}/C_{D(10V)}$		2.25	2.5	2.75	—
Series resistance*	r_D	$C_D = 9 \text{ pF}, f = 470 \text{ MHz}$		0.18	0.22	Ω

Note) 1. Rated input/output frequency: 470 MHz

2. *: r_f measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

